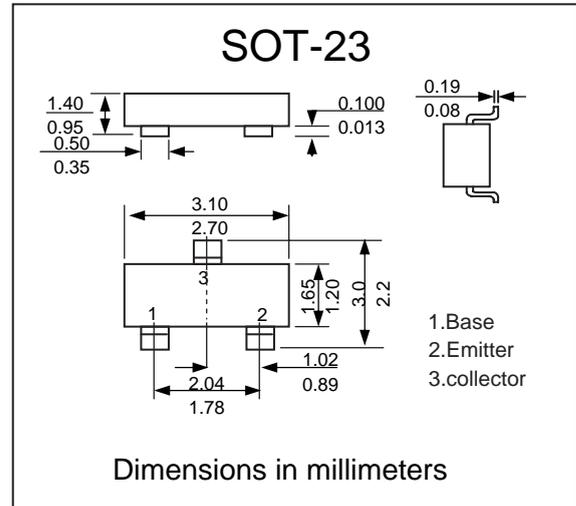


NPN TRANSISTOR

MMBT3904

FEATURES

- Complementary to MMBT3906



Marking: 1AM

MAXIMUM RATINGS (Ta=25 unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector–Base Voltage	V_{CBO}	60	V
Collector–Emitter Voltage	V_{CEO}	40	V
Emitter–Base Voltage	V_{EBO}	6	V
Collector Current — Continuous	I_C	200	mA
Collector Power Dissipation	P_C	200	mW
Thermal Resistance From Junction To Ambient	R_{thJA}	625	°C/W
Operation Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	°C

CLASSIFICATION OF hFE

HFE	100 - 300	
Rank	L	H
Range	100 - 200	200 - 300

ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwise noted.)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\mu A, I_E = 0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1\text{ mA}, I_B = 0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	6			V
Collector cut-off current	I_{CEX}	$V_{CE} = 30V, V_{BE(off)} = 3V$			50	nA
Collector cut-off current	I_{CBO}	$V_{CB} = 60V, I_E = 0$			100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$			100	nA
DC current gain	h_{FE1}	$V_{CE} = 1V, I_C = 10\text{mA}$	100		300	
	h_{FE2}	$V_{CE} = 1V, I_C = 50\text{mA}$	60			
	h_{FE3}	$V_{CE} = 1V, I_C = 100\text{mA}$	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 50\text{mA}, I_B = 5\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 50\text{mA}, I_B = 5\text{mA}$			0.95	V
Transition frequency	f_T	$V_{CE} = 20V, I_C = 10\text{mA}, f = 100\text{MHz}$	300			MHZ
Delay time	t_d	$V_{CC} = 3V, V_{BE(off)} = -0.5V, I_C = 10\text{mA}, I_{B1} = 1\text{mA}$			35	ns
Rise time	t_r				35	ns
Storage time	t_s	$V_{CC} = 3V, I_C = 10\text{mA}, I_{B1} = I_{B2} = 1\text{mA}$			200	ns
Fall time	t_f				50	ns

RATING RATING AND CHARACTERISTIC CURVES (MMBT3904)

